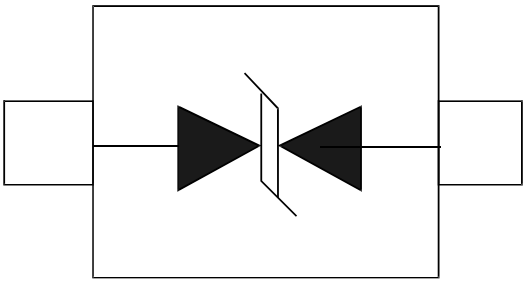
Features

- 320W peak pulse power (tp = 8/20μs)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2 ±30kV contact ±30kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 10A (8/20μs)



SOD-323

Applications

- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Pagers Peripherals

Mechanical Data

- SOD323 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Absolute Maximum Rating

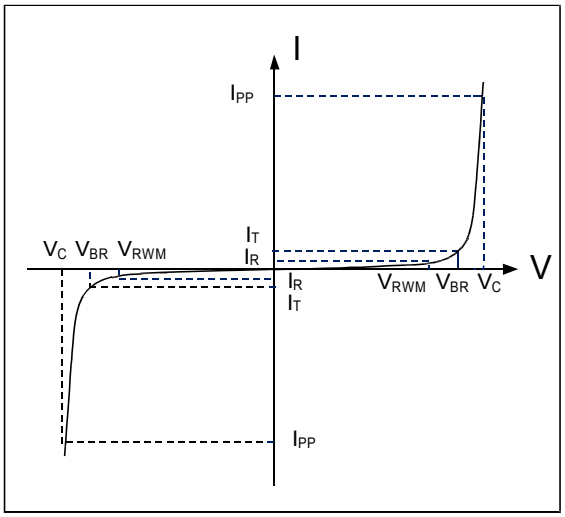
Rating	Symbol	Value	Units
Peak Pulse Power (t_p =8/20μs)	P_{PP}	320	W
Peak Pulse Current (t_p =8/20μs) (note1)	I_{pp}	10	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	30 30	kV
Lead Soldering Temperature	T_L	260	℃
Junction Temperature	T_J	-55 to + 150	℃
Storage Temperature	T_{stg}	-55 to + 150	℃

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				15.0	V
Reverse Breakdown Voltage	V_{BR}	I_T=1mA	16.7			V
Reverse Leakage Current	I_R	V_{RWM}=15V,T=25℃			0.5	uA
Clamping Voltage	V_C	I_{PP}=10A,t_p=8/20μs			32	V
Junction Capacitance	C_j	V_R = 0V, f = 1MHz		20		pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current



Note:. 8/20μs pulsewaveform.

Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

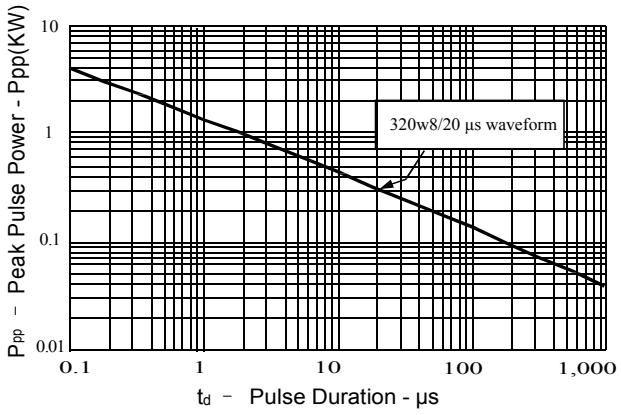


Figure 2: Power Derating Curve

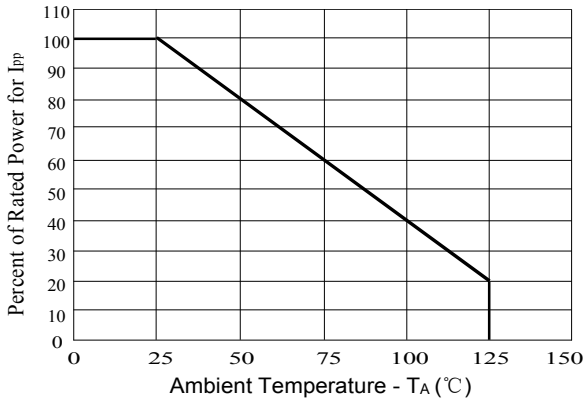


Figure3: Pulse Waveform

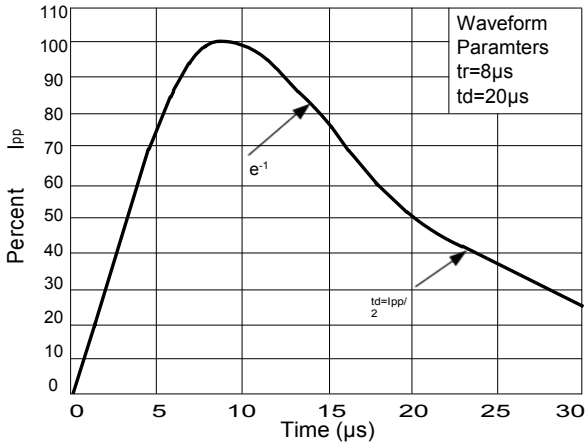


Figure 4: Clamping Voltage vs.Ipp